

CSD83325L 12-V Dual N-Channel NexFET™ Power MOSFET

1 Features

- Common Drain Configuration
- Low-On Resistance
- Small Footprint of 2.2 mm × 1.15 mm
- Lead Free
- RoHS Compliant
- Halogen Free
- Gate ESD Protection

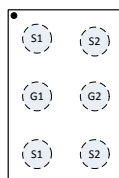
2 Applications

- Battery Management
- Battery Protection

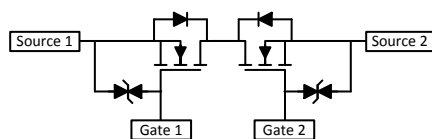
3 Description

This 12-V, 9.9-mΩ, 2.2-mm × 1.15-mm LGA Dual NexFET™ power MOSFET is designed to minimize resistance and gate charge in a small footprint. Its small footprint and common drain configuration make the device ideal for battery pack applications in small handheld devices.

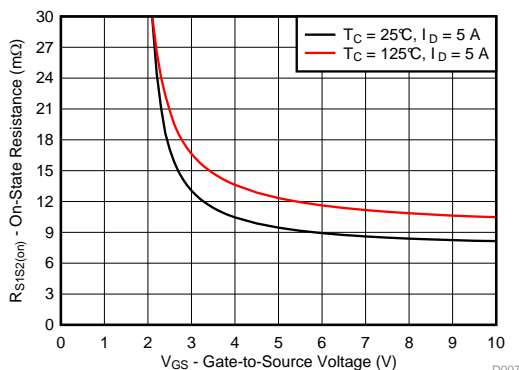
Top View



Configuration



$R_{DS(on)}$ vs V_{GS}



D007

Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE	UNIT
V_{S1S2}	Source-to-Source Voltage	12	V
Q_g	Gate Charge Total (4.5 V)	8.4	nC
Q_{gd}	Gate Charge Gate-to-Drain	1.9	nC
$R_{S1S2(on)}$	Source-to-Source On Resistance	$V_{GS} = 2.5\text{ V}$	17.5 mΩ
		$V_{GS} = 3.8\text{ V}$	10.9 mΩ
		$V_{GS} = 4.5\text{ V}$	9.9 mΩ
$V_{GS(th)}$	Threshold Voltage	0.95	V

Device Information⁽¹⁾

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD83325L	3000	7-Inch Reel	2.20-mm × 1.15-mm Land Grid Array (LGA) Package	Tape and Reel
CSD83325LT	250			

(1) For all available packages, see the orderable addendum at the end of the data sheet.

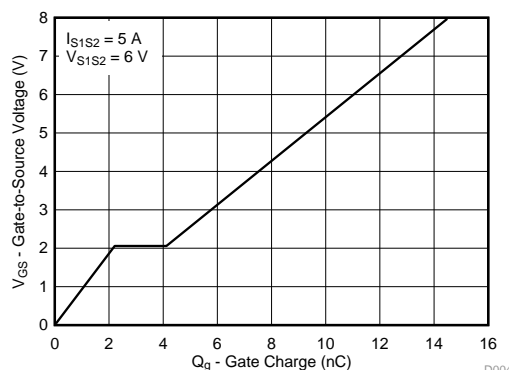
Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$		VALUE	UNIT
V_{S1S2}	Source-to-Source Voltage	12	V
V_{GS}	Gate-to-Source Voltage	±10	V
I_S	Continuous Source Current ⁽¹⁾	8	A
I_{SM}	Pulsed Source Current ⁽²⁾	52	A
P_D	Power Dissipation	2.3	W
$V_{(ESD)}$	Human-Body Model (HBM)	2000	V
T_J, T_{stg}	Operating Junction Temperature, Storage Temperature	-55 to 150	°C

(1) Device operating at a temperature of 105°C.

(2) Typical min $Cu R_{\theta JA} = 150^\circ\text{C/W}$, pulse duration $\leq 100\ \mu\text{s}$, duty cycle $\leq 1\%$.

Gate Charge



D004



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (January 2016) to Revision B	Page
• Added Diode Characteristics ($V_{F(S-S)}$) in the <i>Electrical Characteristics</i> table	3
• Added Figure 9 to <i>Typical MOSFET Characteristics</i> section	4
• Added <i>Receiving Notification of Documentation Updates</i> section to <i>Device and Documentation Support</i> section.....	7

Changes from Original (November 2014) to Revision A	Page
• Improved graph setup for readability	4
• Added Community Resources	7

5 Specifications

5.1 Electrical Characteristics

 $T_A = 25^\circ\text{C}$ (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{S1S2}	Source-to-source voltage	$V_{GS} = 0\text{ V}, I_S = 250\ \mu\text{A}$	12			V
I_{S1S2}	Source-to-source leakage current	$V_{GS} = 0\text{ V}, V_{S1S2} = 9.6\text{ V}$			1	μA
I_{GSS}	Gate-to-source leakage current	$V_{S1S2} = 0\text{ V}, V_{GS} = 10\text{ V}$			10	μA
$V_{GS(th)}$	Gate-to-source threshold voltage	$V_{S1S2} = V_{GS}, I_S = 250\ \mu\text{A}$	0.75	0.95	1.25	V
$R_{S1S2(on)}$	Source-to-source on resistance	$V_{GS} = 2.5\text{ V}, I_S = 5\text{ A}$	14.0	17.5	23.0	$\text{m}\Omega$
		$V_{GS} = 3.8\text{ V}, I_S = 5\text{ A}$	8.8	10.9	13.0	$\text{m}\Omega$
		$V_{GS} = 4.5\text{ V}, I_S = 5\text{ A}$	7.9	9.9	11.9	$\text{m}\Omega$
g_{fs}	Transconductance	$V_{S1S2} = 1.2\text{ V}, I_S = 5\text{ A}$		36		S
DYNAMIC CHARACTERISTICS⁽¹⁾						
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}, V_{S1S2} = 6\text{ V}, f = 1\text{ MHz}$		902	1170	pF
C_{oss}	Output capacitance			187	243	pF
C_{rss}	Reverse transfer capacitance			111	144	pF
Q_g	Gate charge total (4.5 V)	$V_{S1S2} = 6\text{ V}, I_S = 5\text{ A}$		8.4	10.9	nC
Q_{gd}	Gate charge gate-to-drain			1.9		nC
Q_{gs}	Gate charge gate-to-source			2.2		nC
$Q_{g(th)}$	Gate charge at V_{th}			0.6		nC
Q_{oss}	Output charge		$V_{S1S2} = 6\text{ V}, V_{GS} = 0\text{ V}$		2.9	
$t_{d(on)}$	Turnon delay time	$V_{S1S2} = 6\text{ V}, V_{GS} = 4.5\text{ V}, I_{S1S2} = 5\text{ A}, R_G = 0\ \Omega$		205		ns
t_r	Rise time			353		ns
$t_{d(off)}$	Turnoff delay time			711		ns
t_f	Fall time			589		ns
DIODE CHARACTERISTICS						
$V_{F(S-S)}$	Source-to-source diode forward voltage	$I_{SS} = 5\text{ A}, V_{G1S1} = 0\text{ V}, V_{G2S2} = 4.5\text{ V}$		0.79	1.0	V

(1) Dynamic characteristics values specified are per single FET.

5.2 Thermal Information

 $T_A = 25^\circ\text{C}$ (unless otherwise stated)

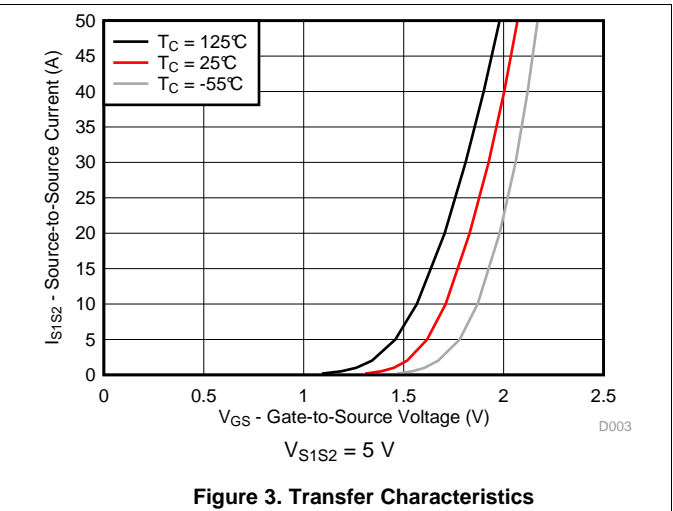
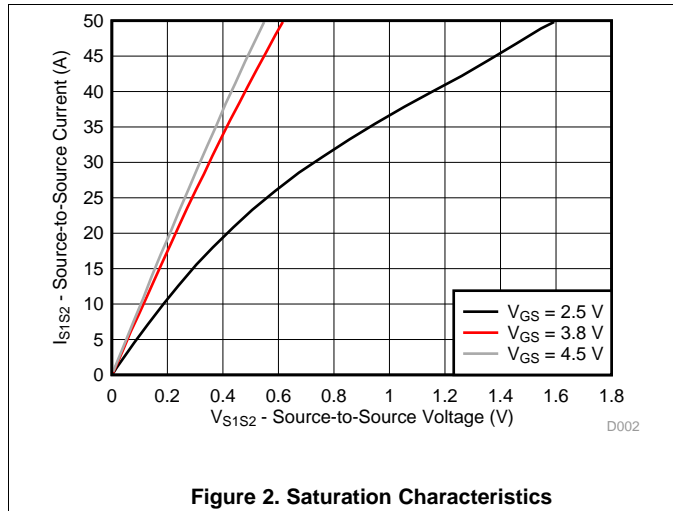
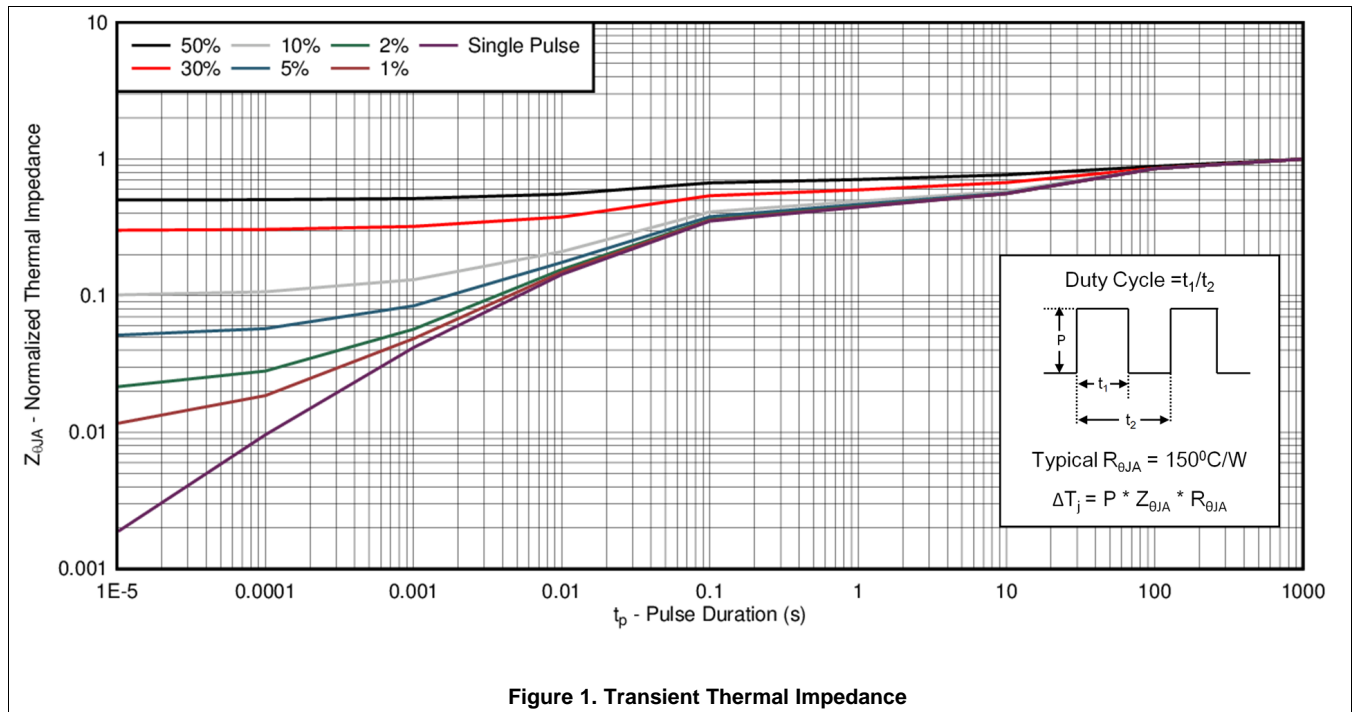
THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾		150		$^\circ\text{C/W}$
	Junction-to-ambient thermal resistance ⁽²⁾		55		

(1) Device mounted on FR4 material with minimum Cu mounting area.

(2) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.

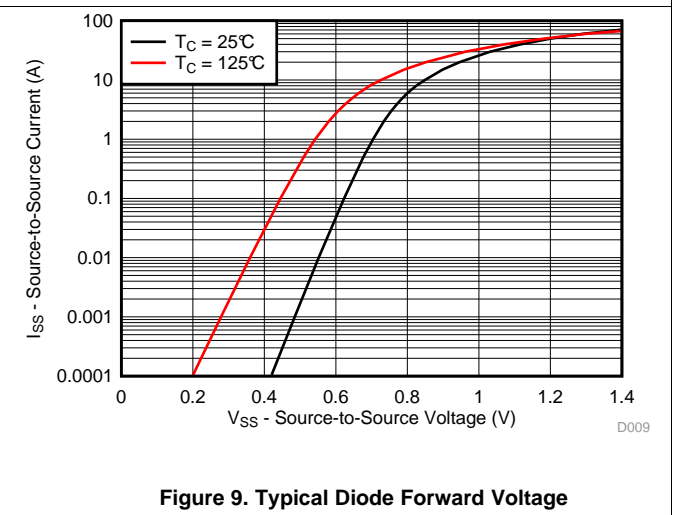
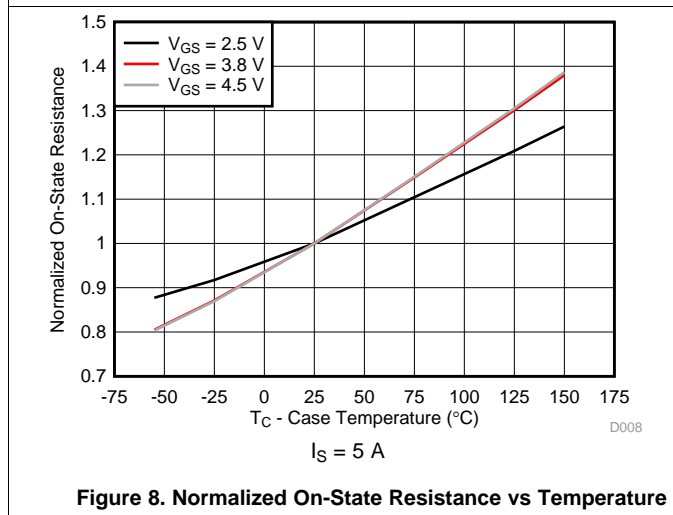
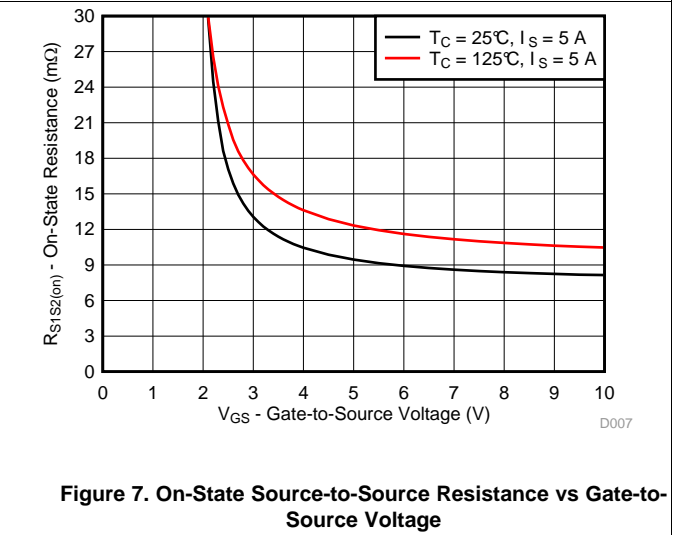
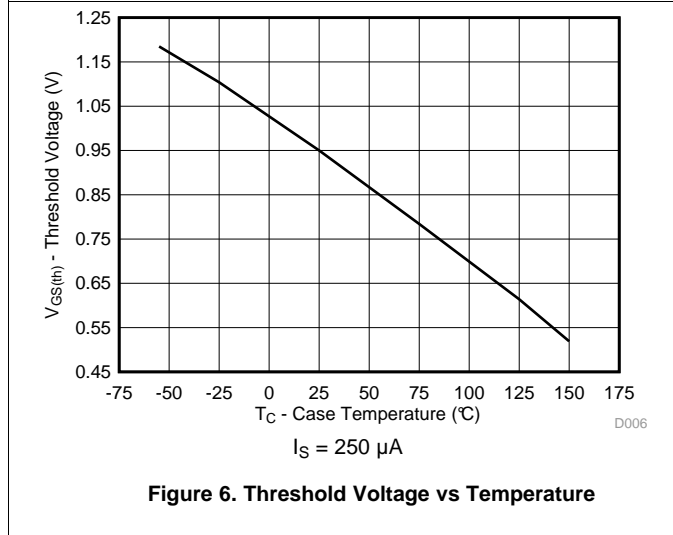
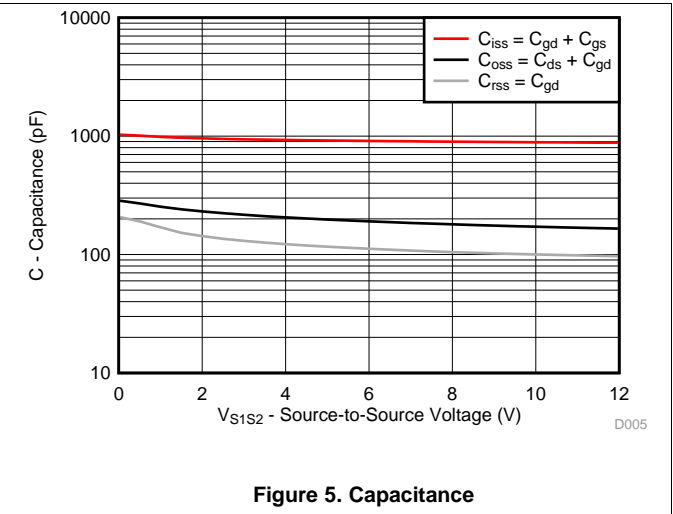
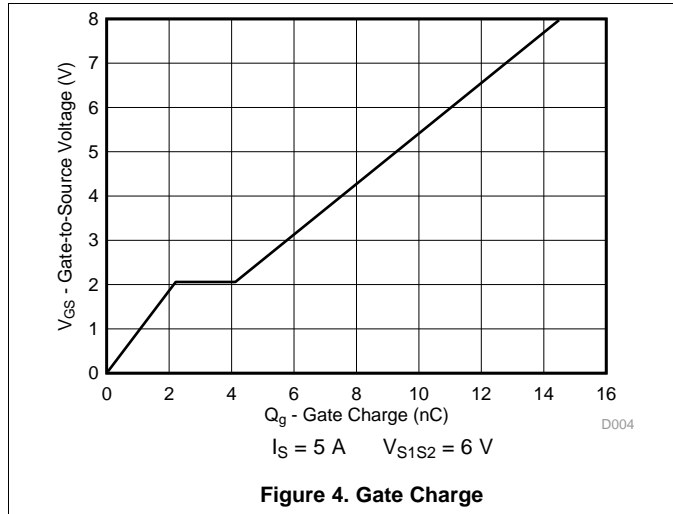
5.3 Typical MOSFET Characteristics

T_A = 25°C (unless otherwise stated)



Typical MOSFET Characteristics (continued)

T_A = 25°C (unless otherwise stated)



Typical MOSFET Characteristics (continued)

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

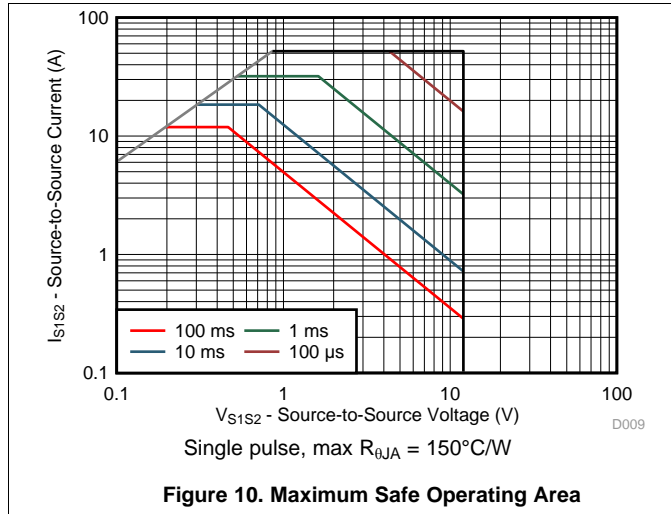


Figure 10. Maximum Safe Operating Area

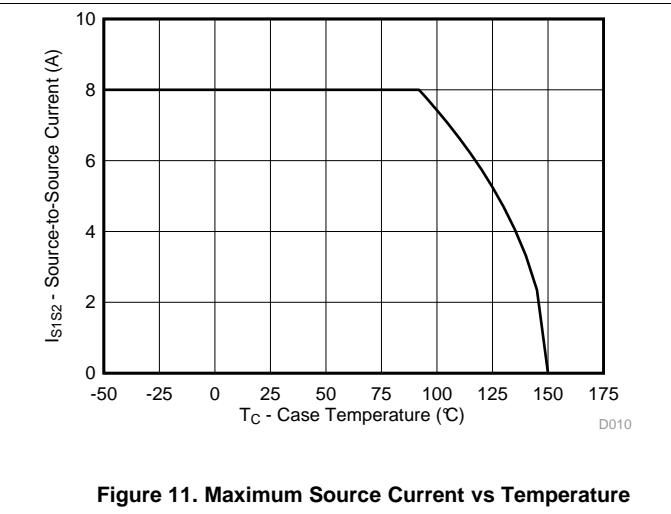


Figure 11. Maximum Source Current vs Temperature

6 Device and Documentation Support

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.3 Trademarks

NexFET, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

6.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.5 Glossary

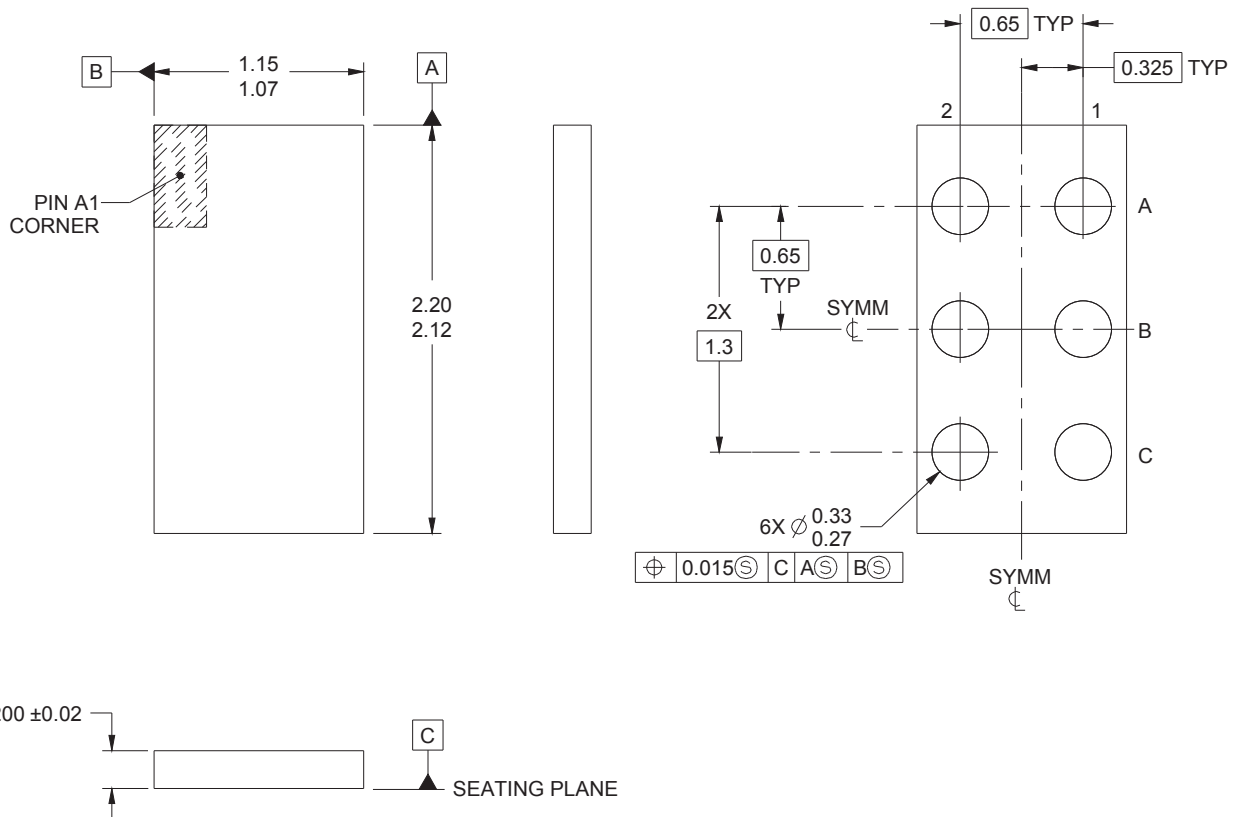
[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 Mechanical, Packaging, and Orderable Information

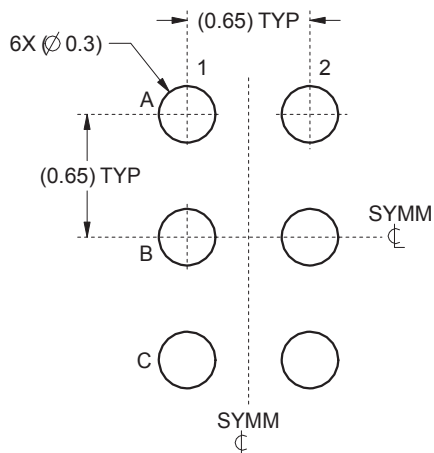
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Package Dimensions

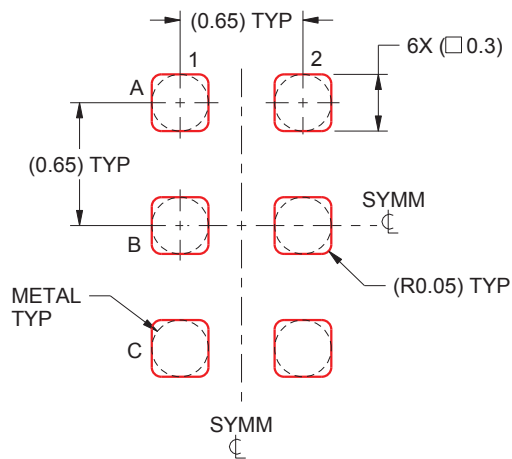


All dimensions in millimeters.

7.2 Recommended PCB Pattern



7.3 Recommended Stencil Pattern



All dimensions are in millimeters.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD83325L	ACTIVE	PICOSTAR	YJE	6	3000	RoHS & Green	NIAU	Level-1-260C-UNLIM		83325L	Samples
CSD83325LT	ACTIVE	PICOSTAR	YJE	6	250	RoHS & Green	NIAU	Level-1-260C-UNLIM	-55 to 150	83325L	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD83325L	PICOST AR	YJE	6	3000	178.0	8.4	1.25	2.34	0.32	4.0	8.0	Q1
CSD83325LT	PICOST AR	YJE	6	250	178.0	8.4	1.25	2.34	0.32	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD83325L	PICOSTAR	YJE	6	3000	220.0	220.0	35.0
CSD83325LT	PICOSTAR	YJE	6	250	220.0	220.0	35.0

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